

Abstract

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[Object] To provide a sputtering target for producing an oxide semiconductor thin film having high

5 properties, which serves as a substitute for IGZO, and a method of producing the same.

[Solving Means] In order to achieve the above-mentioned object, a sputtering target according to an embodiment of the present invention includes: an oxide
10 sintered body including indium, tin, and germanium, in which an atom ratio of germanium with respect to a total of indium, tin, and germanium is 0.07 or more and 0.40 or less, and an atom ratio of tin with respect to the total of indium, tin, and germanium is 0.04 or more
15 and 0.60 or less. As a result, it is possible to achieve transistor characteristics of having mobility of $10 \text{ cm}^2/\text{Vs}$ or more.

[Selected Drawing] Fig. 1